

(Transistor)

2SA2002

For High Current Application
Silicon PNP Epitaxial Type Micro(Frame type)

DESCRIPTION

2SA2002 is a silicon PNP epitaxial type transistor designed with high collector current, small $V_{CE(sat)}$.

FEATURE

- High collector current
 $I_{CM} = -1000\text{mA}$
- Low collector to emitter saturation voltage
 $V_{CE(sat)} = -0.25\text{V typ}$
- Excellent linearity of DC forward current gain
- High gain band width product
 $f_T = 180\text{MHz typ}$
- High collector dissipation
 $P_c = 600\text{mW}$

APPLICATION

Small type motor drive, relay drive, power supply application.

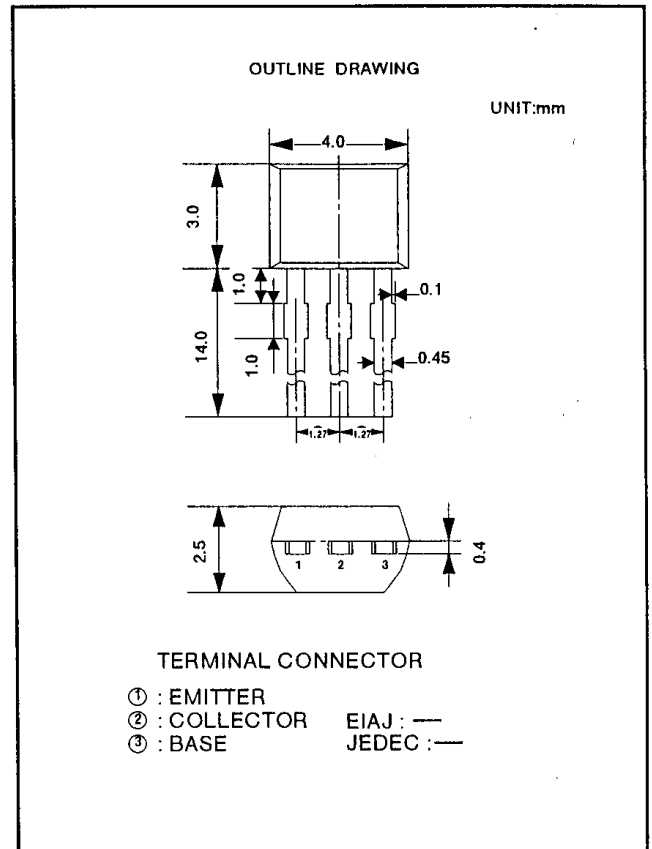
MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	RATINGS	UNIT
V_{CBO}	Collector to Base voltage	-25	V
V_{EBO}	Emitter to Base voltage	-4	V
V_{CEO}	Collector to Emitter voltage	-20	V
I_{CM}	Peak collector current	-1000	mA
I_C	Collector current	-700	mA
P_c	Collector to Base voltage	600	mW
T_J	Junction temperature	+150	$^\circ\text{C}$
T_{stg}	Storage temperature	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
$V_{(BR)CBO}$	C to B break down voltage	$I_C = -10\mu\text{A}, I_E = 0$	-25			V
$V_{(BR)EBO}$	E to B break down voltage	$I_E = -10\mu\text{A}, I_C = 0$	-4			V
$V_{(BR)CEO}$	C to E break down voltage	$I_C = -100\mu\text{A}, R_{BE} = \infty$	-20			V
I_{CBO}	Collector cut off current	$V_{CB} = -25\text{V}, I_E = 0$			-1	μA
I_{EBO}	Emitter cut off current	$V_{EB} = -2\text{V}, I_C = 0$			-1	μA
h_{FE}^*	DC forward current gain	$V_{CE} = -4\text{V}, I_C = -100\text{mA}$	150		800	—
$V_{CE(sat)}$	C to E saturation voltage	$I_C = -500\text{mA}, I_B = -25\text{mA}$		-0.25	-0.5	V
f_T	Gain band width product	$V_{CE} = -6\text{V}, I_E = 10\text{mA}$		180		MHz

ITEM	E	F	G
h_{FE}	150~300	250~500	400~800



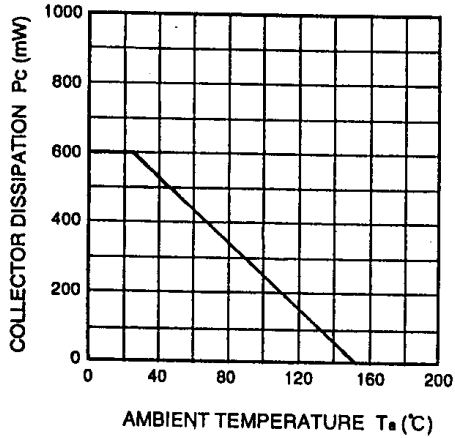
(Transistor)

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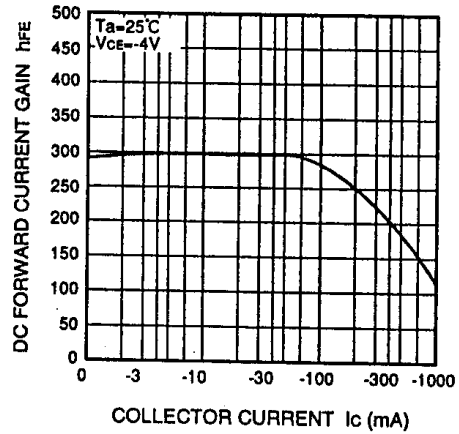
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TYPICAL CHARACTERISTICS

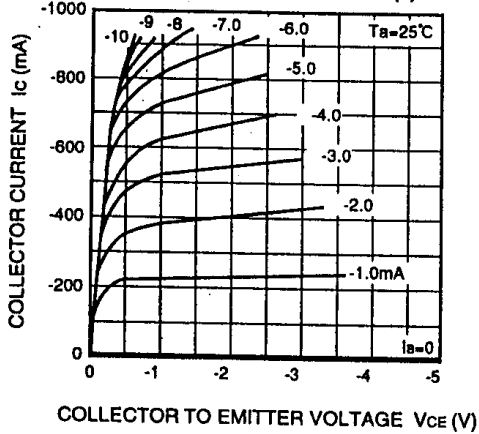
COLLECTOR DISSIPATION VS.
AMBIENT TEMPERATURE



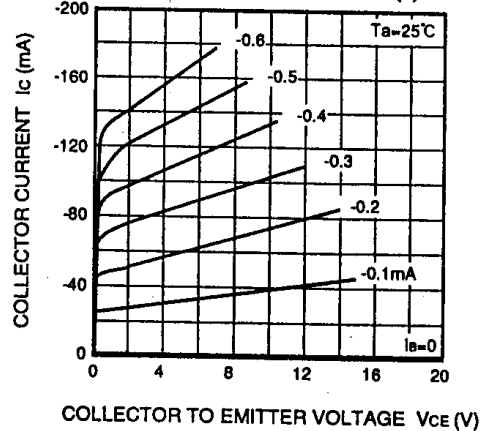
DC FORWARD CURRENT GAIN
VS. COLLECTOR CURRENT



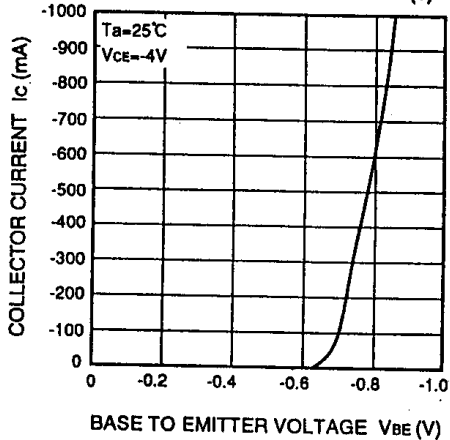
COMMON EMITTER OUTPUT (1)



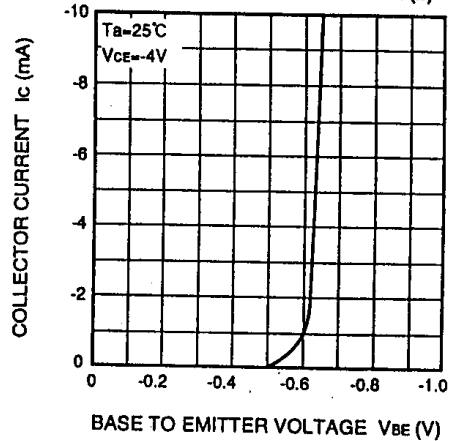
COMMON EMITTER OUTPUT (2)



COMMON EMITTER TRANSFER (1)



COMMON EMITTER TRANSFER (2)



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